



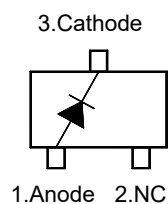
BAS19~BAS20

Silicon Epitaxial Planar Switching Diode

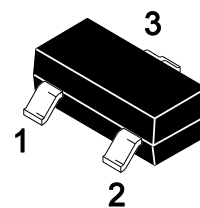
Features

- High voltage
- Small package
- Small capacitance

Equivalent Circuit



SOT-23



1.Anode 2.NC 3.Cathode

Marking Code :

BAS19 : FC

BAS20 : GC

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_{RRM}	120	V
		200	
Continuous Forward Current	$I_{F(AV)}$	200	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5	A
		2.5	
Power Dissipation	P_D	350	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	357	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^{\circ}\text{C}$



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Electrical Characteristics (T_A=25°C)

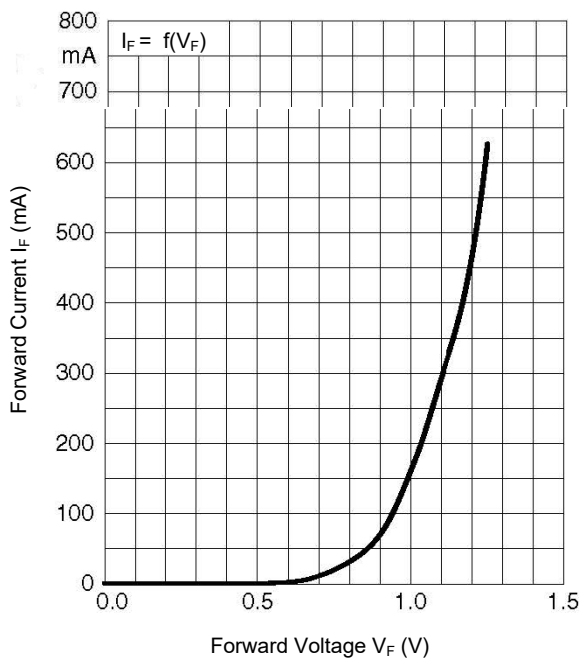
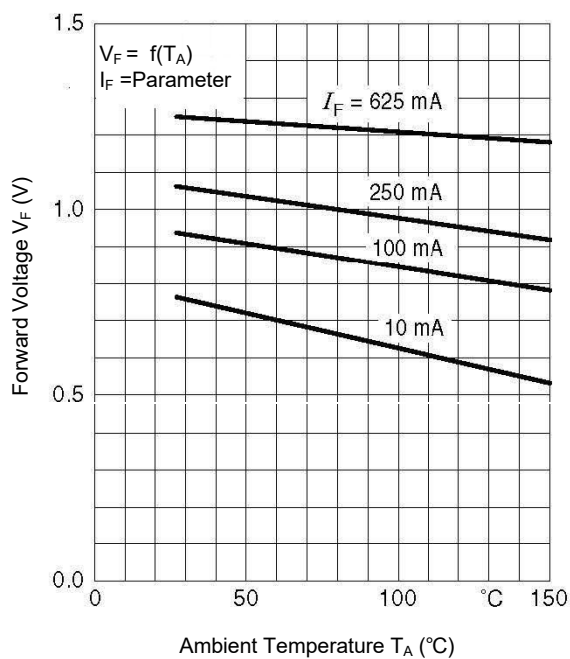
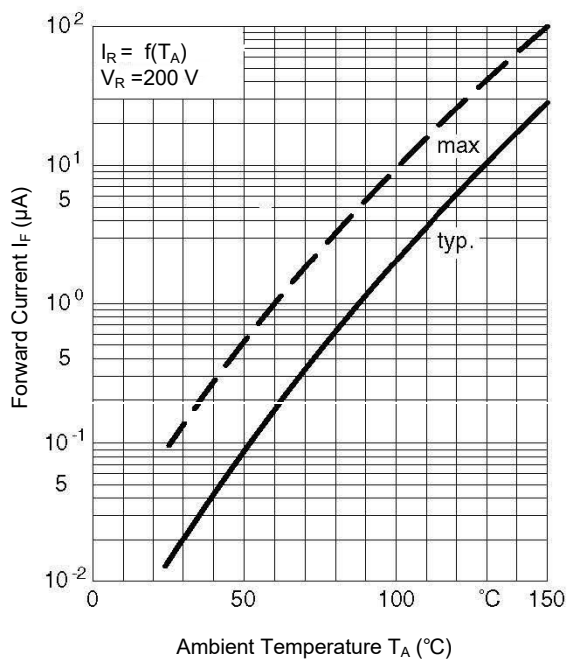
Parameter		Symbol	Min.	Max.	Unit
Forward Voltage					
at I _F = 100 mA		V _F	--	1	V
at I _F = 200 mA			--	1.25	
Reverse Breakdown Voltage					
at I _R = 100 μA	BAS19	V _R	120	--	V
at I _R = 100 μA	BAS20		200	--	
Reverse Current					
at V _R = 100 V	BAS19	I _R	--	0.1	μA
at V _R = 150 V	BAS20		--	0.1	
at V _R = 100 V, at T _J = 150 °C	BAS19		--	100	
at V _R = 150 V, at T _J = 150 °C	BAS20		--	100	
Typical Junction Capacitance					
at V _R = 0 V, f = 1 MHz		C _j	--	5	pF
Maximum Reverse Recovery Time					
at I _F = I _R = 30 mA, I _{R(REC)} = 3 mA, R _L = 100 Ω		T _{rr}	--	50	nS



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Typical Characteristic Curves





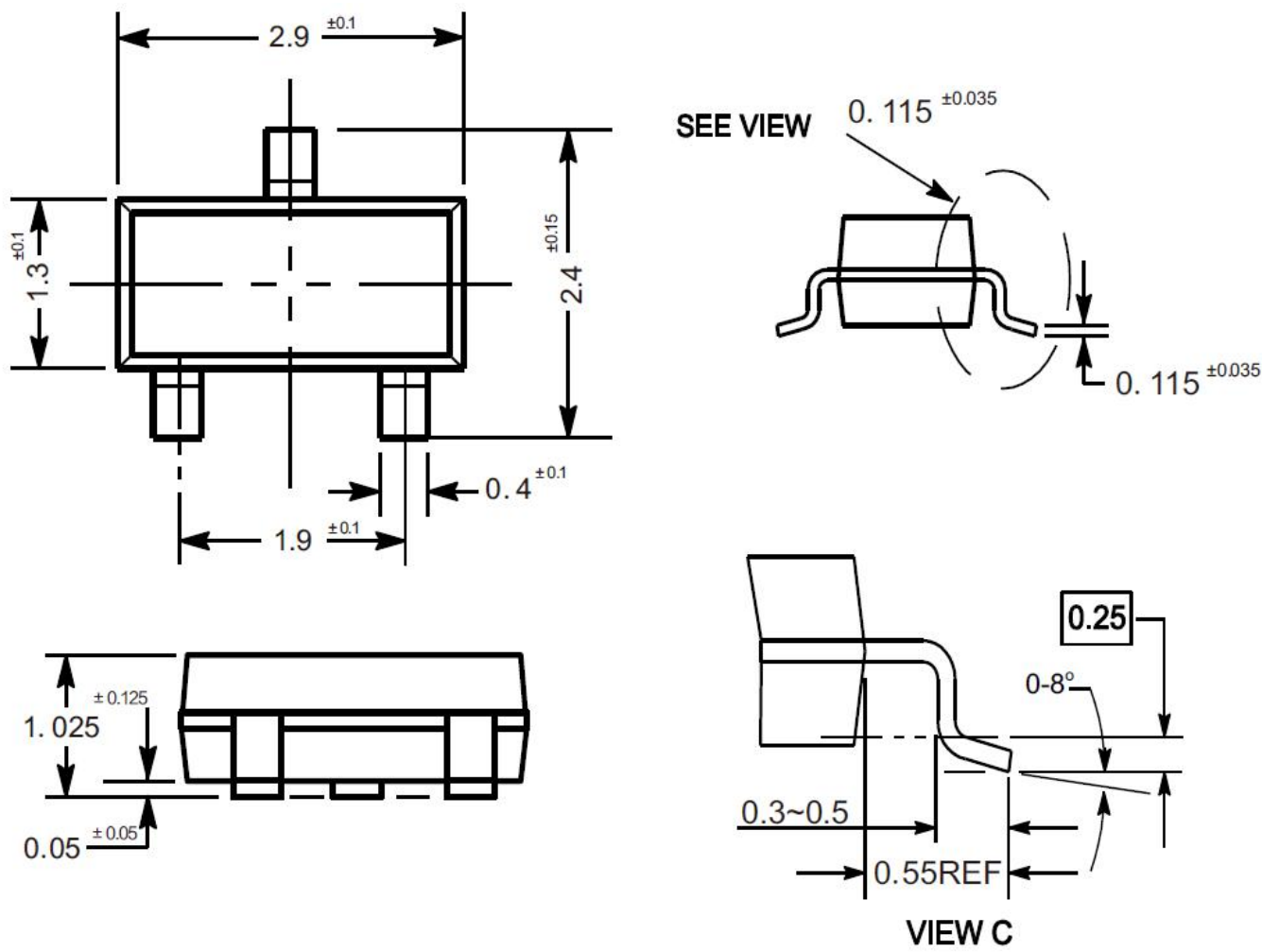
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Package Outline

SOT-23

Dimensions in mm



Ordering Information

Device	Package	Shipping
BAS19~BAS20	SOT-23	3,000PCS/Reel&7inches